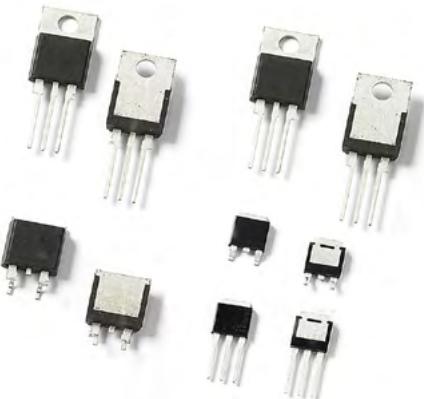


SJxx12xx series

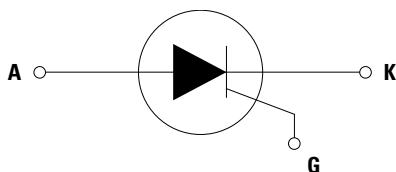


Agency Approvals

Agency	Agency File Number
	E71639*

* - L Package Only

Schematic Symbol



Description

This SJxx12xx high junction temperature SCR series is ideal for uni-directional switch applications such as phase control in heating, motor speed controls, converters/rectifiers, inrush current control and capacitive discharge ignitions.

These SCRs have a low gate current trigger level of 6mA, 10mA or 20mA maximum at approximately 1.5V.

Features & Benefits

- Halogen free and RoHS compliant
- 150°C maximum junction temperature
- Surge capability up to 120 A at 60 Hz half cycle
- Recognized to UL 1557 as an Electrically Isolated Semiconductor Device

Applications

Typical applications are capacitive discharge systems for strobe lights, nailers, staplers and gas engine ignition. Additional applications include various AC to DC applications, low power AC motor and controls for power tools, home/brown goods and white goods appliances.

Internally constructed isolated packages are offered for ease of heat sinking with high isolation voltage.

Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	12	A
V_{DRM}/V_{RRM}	400 or 600	V
I_{GT}	6 - 20	mA

Absolute Maximum Ratings

Symbol	Parameter	Test Conditions	Value	Unit
V_{DSM}/V_{RSM}	Peak non-repetitive blocking voltage	PW=100 μs	$V_{DRM}/V_{RRM}+100$	V
$I_{T(RMS)}$	RMS on-state current	SJxx12Lx	12	A
		SJxx12Rx SJxx12Nx		
		SJxx12Dx SJxx12Vx		
$I_{T(AV)}$	Average on-state current	SJxx12Lx	7.6	A
		SJxx12Rx SJxx12Ny		
		SJxx12Dx SJxx12Vx		
I_{TSM}	Peak non-repetitive surge current (single half cycle, T_j (initial) = 25°C)	f = 50Hz	100	A
		f = 60Hz	120	
I^2t	I^2t Value for fusing	$t_p = 8.3$ ms	60	A ² s
di/dt	Critical rate of rise of on-state current	f = 60Hz; T_j = 150°C	100	A/μs
I_{GM}	Peak gate current	T_j = 150°C	2	A
$P_{G(AV)}$	Average gate power dissipation	T_j = 150°C	0.5	W
T_{stg}	Storage temperature range		-40 to 150	°C
T_j	Operating junction temperature range		-40 to 150	

Electrical Characteristics ($T_j = 25^\circ\text{C}$, unless otherwise specified) - TO-220L ,TO-220R and TO-263 package

Symbol	Test Conditions		SJxx12x	SJxx12x1	SJxx12x2	Unit
I_{GT}	$V_D = 12\text{V}$ $R_L = 60 \Omega$	MAX.	20	6	10	mA
		MIN.	8	2	5	
V_{GT}	$V_D = 12\text{V}$ $R_L = 60 \Omega$	MAX.	1.5	1.5	1.5	V
dv/dt	$V_D = 67\% V_{DRM}$; gate open; $T_j = 125^\circ\text{C}$	MIN.	800	70	500	V/ μs
	$V_D = 67\% V_{DRM}$; gate open; $T_j = 150^\circ\text{C}$		400	-	200	
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3 \text{k}\Omega$ $T_j = 125^\circ\text{C}$	MIN.	0.2	0.2	0.2	V
I_H	$I_T = 200\text{mA}$ (initial)	MAX.	60	15	35	mA
t_q	$I_T = 2\text{A}$; $t_p = 50\mu\text{s}$; dv/dt = 5V/ μs ; di/dt = 30A/ μs	MAX.	40	40	40	μs
t_{gt}	$I_G = 2 \times I_{GT}$ PW = 15 μs $I_T = 24\text{A}$	TYP.	2	2	2	μs

Note: xx=voltage/10, x=package

Electrical Characteristics ($T_j = 25^\circ\text{C}$, unless otherwise specified) - TO-251 and TO-252 package

Symbol	Test Conditions	Value		Unit	
		SJxx12x1	SJxx12x		
I_{GT}	$V_D = 12\text{V}$ $R_L = 60 \Omega$	MAX.	6	mA	
		MIN.	2		
		MAX.	1.5	V	
dv/dt	$V_D = V_{DRM}$; gate open; $T_j = 125^\circ\text{C}$	400V	MIN.	V/ μs	
		600V			
		400V	50		
		600V	10		
			250		
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3 \text{k}\Omega$ $T_j = 125^\circ\text{C}$		0.2	V	
	$V_D = V_{DRM}$ $R_L = 3.3 \text{k}\Omega$ $T_j = 150^\circ\text{C}$		0.1		
I_H	$I_T = 200\text{mA}$ (initial)	MAX.	20	40	mA
t_q	$I_T = 2\text{A}$; $t_p = 50\mu\text{s}$; dv/dt = 5V/ μs ; di/dt = 30A/ μs	MAX.	35	35	μs
t_{gt}	$I_G = 2 \times I_{GT}$ PW = 15 μs $I_T = 12\text{A}$	TYP.	0.5	2	μs

Note: xx=voltage/10, x=package

Static Characteristics

Symbol	Test Conditions		Value	Unit
V_{TM}	Component $I_T = 32\text{A}$; $t_p = 380 \mu\text{s}$	MAX.	1.6	V
I_{DRM} / I_{RRM}	$V_{DRM} = V_{RRM}$	$T_j = 25^\circ\text{C}$	MAX.	μA
		$T_j = 125^\circ\text{C}$		
		$T_j = 150^\circ\text{C}$		

Thermal Resistances

Symbol	Parameter		Value	Unit
$R_{\theta(JC)}$	Junction to case (AC)	$SJxx12Lx$	2.4	$^\circ\text{C}/\text{W}$
		$SJxx12Rx$	1.1	
		$SJxx12Nx$		
		$SJxx12Dx$	1.4	
		$SJxx12Vx$		

Note: xx=voltage/10, x=sensitivity

Figure 1: Normalized DC Gate Trigger Current vs. Junction Temperature

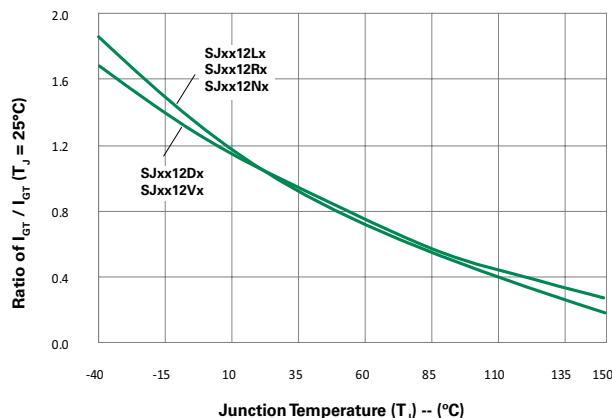


Figure 2: Normalized DC Gate Trigger Voltage vs. Junction Temperature

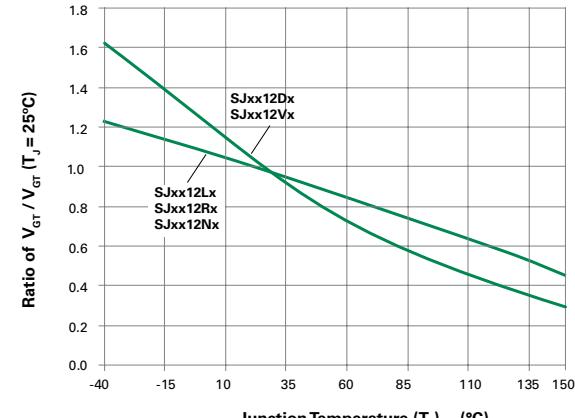


Figure 3: Normalized DC Holding Current vs. Junction Temperature

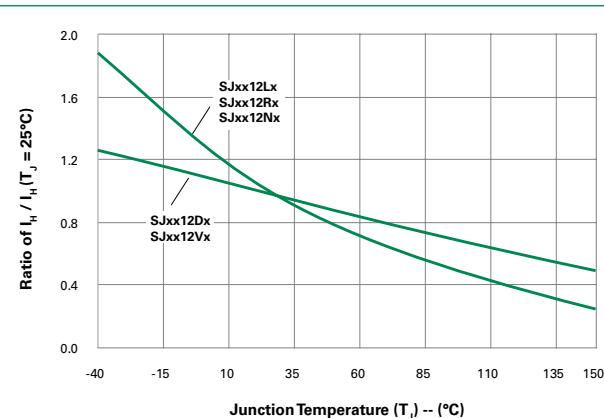


Figure 4: On-State Current vs. On-State Voltage (Typical)

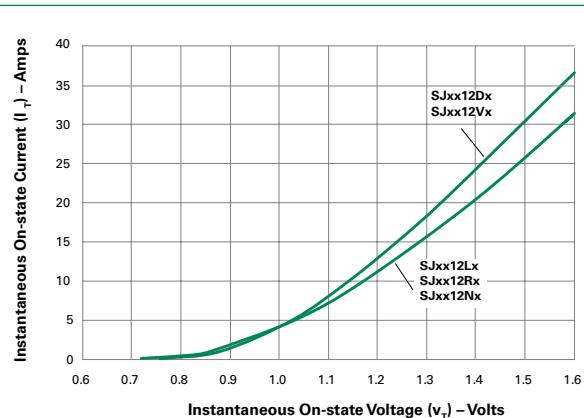


Figure 5: Power Dissipation (Typical) vs. RMS On-State Current

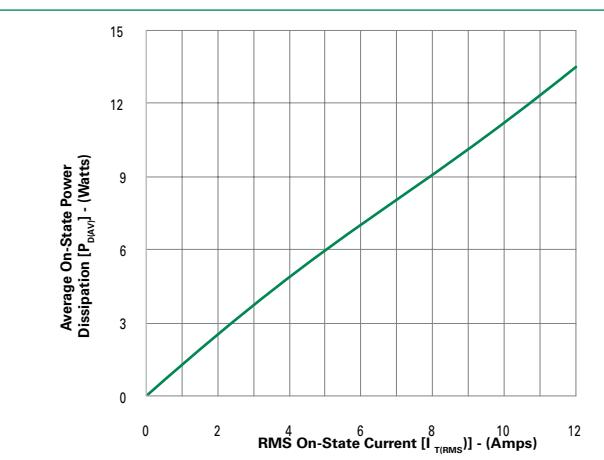


Figure 6: Maximum Allowable Case Temperature vs. RMS On-state Current

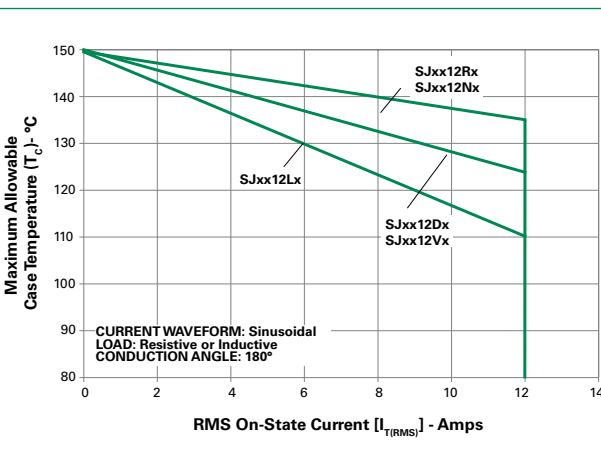


Figure 7: Maximum Allowable Case Temperature vs. Average On-State Current

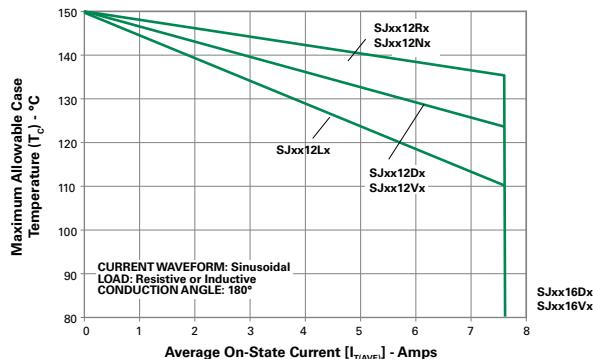


Figure 8: Peak Capacitor Discharge Current

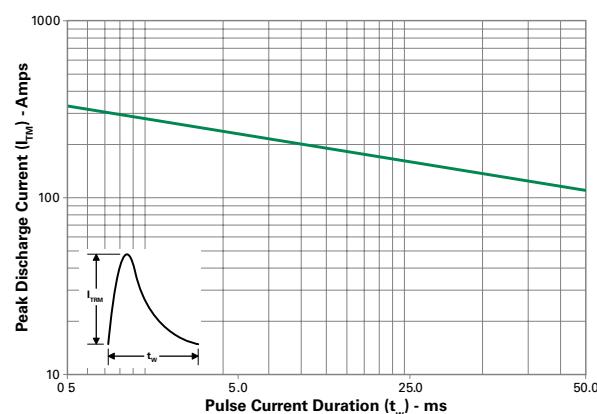


Figure 9: Peak Capacitor Discharge Current Derating

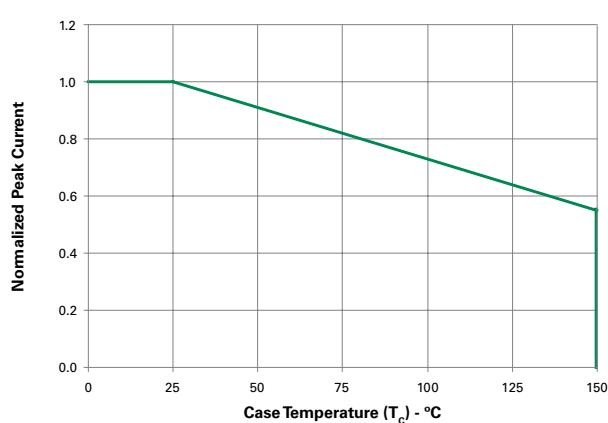
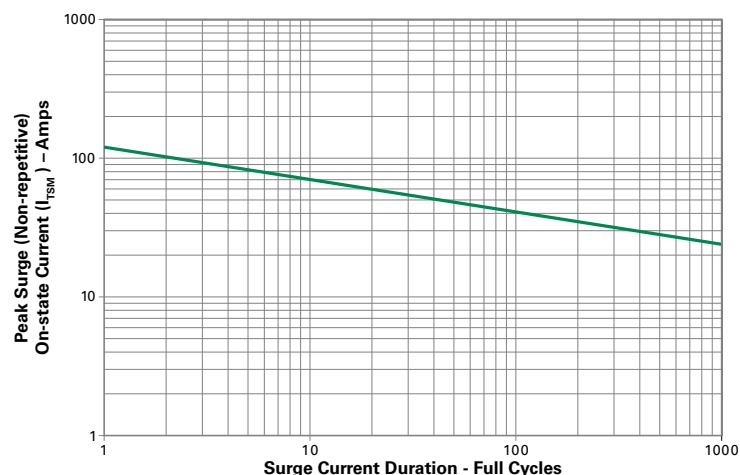


Figure 10: Surge Peak On-State Current vs. Number of Cycles



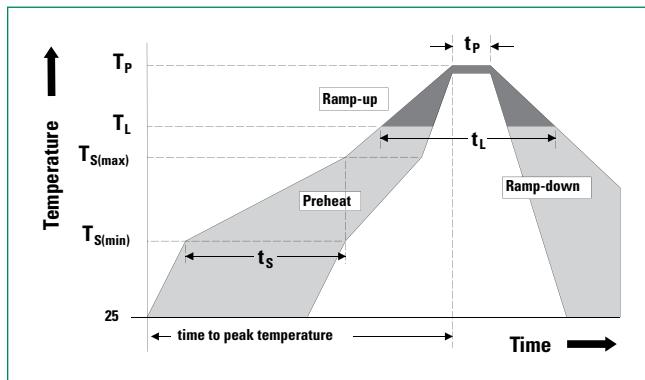
SUPPLY FREQUENCY: 60 Hz Sinusoidal
 LOAD: Resistive
 RMS On-State Current: [$I_{(IRMS)}$]: Maximum Rated Value at Specified Case Temperature

Notes:

1. Gate control may be lost during and immediately following surge current interval.
2. Overload may not be repeated until junction temperature has returned to steady-state rated value.

Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 180 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Time (t_L)	60 – 150 seconds
Peak Temperature (T_p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matte Tin-plated
Body Material	UL Recognized compound meeting flammability rating V-0
Lead Material	Copper Alloy

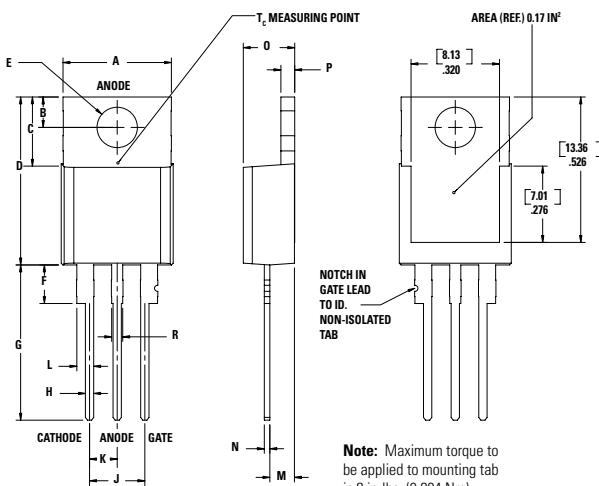
Design Considerations

Careful selection of the correct component for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the component rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Environmental Specifications

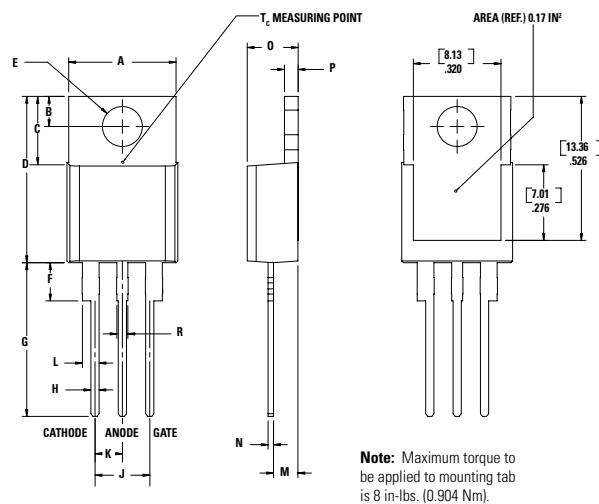
Test	Specifications and Conditions
AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 150°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 1000 cycles; -55°C to +150°C, 15-min dwell-time
Temperature/Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 160V - DC: 85°C, 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Lead Bend	MIL-STD-750, M-2036 Cond E
Moisture Sensitivity Level	Level 1, JEDEC-J-STD-020D

Dimensions — TO-220AB (R-Package) — Non-Isolated Mounting Tab Common with Center Lead



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

Dimensions — TO-220AB (L-Package) — Isolated Mounting Tab

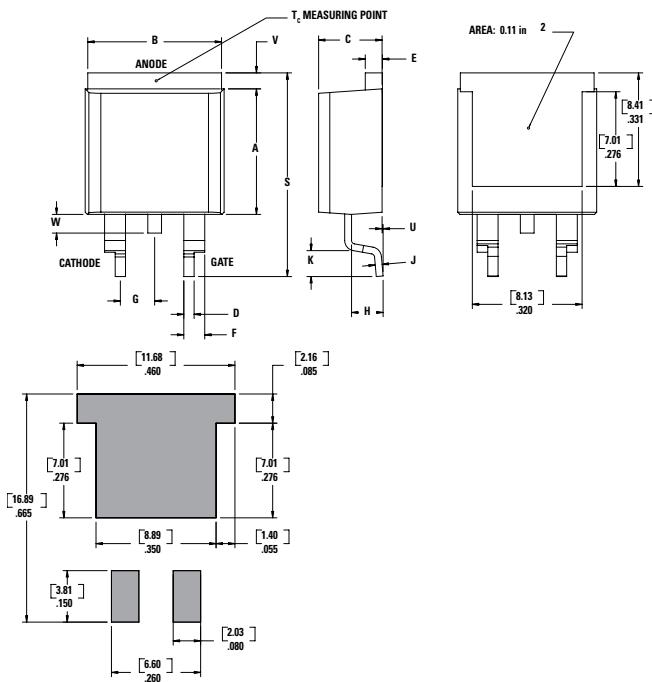


Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

Thyristors

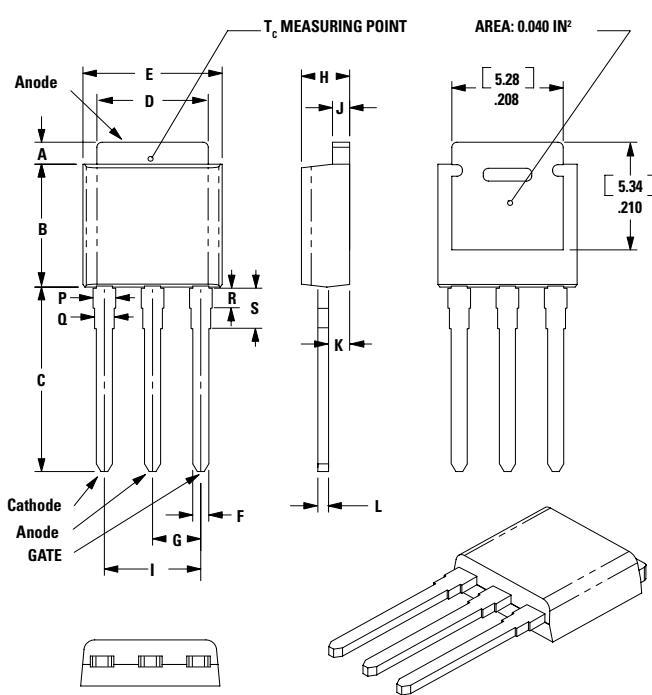
12 Amp High Junction Temperature SCRs

Dimensions — TO-263AB (N-package) — D²-Pak Surface Mount



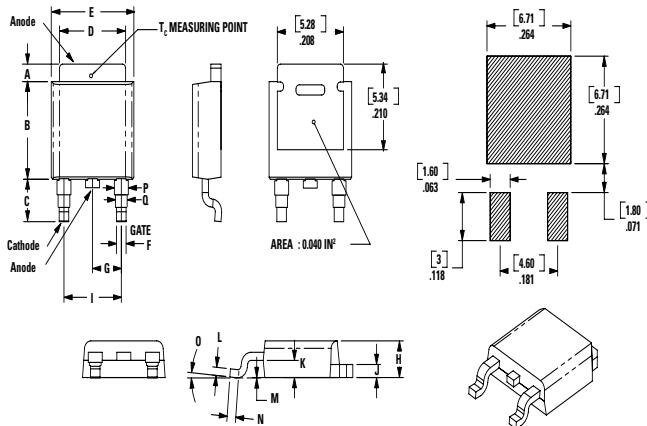
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.360	0.370	9.14	9.40
B	0.380	0.420	9.65	10.67
C	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
E	0.045	0.060	1.14	1.52
F	0.060	0.075	1.52	1.91
G	0.095	0.105	2.41	2.67
H	0.092	0.102	2.34	2.59
J	0.018	0.024	0.46	0.61
K	0.090	0.110	2.29	2.79
S	0.590	0.625	14.99	15.88
V	0.035	0.045	0.89	1.14
U	0.002	0.010	0.05	0.25
W	0.040	0.070	1.02	1.78

Dimensions — TO-251AA (V/I-Package) — V/I-PAK Through Hole



Dimension	Inches			Millimeters		
	Min	Typ	Max	Min	Typ	Max
A	0.040	0.044	0.050	1.02	1.11	1.27
B	0.235	0.242	0.245	5.97	6.15	6.22
C	0.350	0.361	0.375	8.89	9.18	9.53
D	0.205	0.208	0.213	5.21	5.29	5.41
E	0.255	0.262	0.265	6.48	6.66	6.73
F	0.027	0.031	0.033	0.69	0.80	0.84
G	0.087	0.090	0.093	2.21	2.28	2.36
H	0.085	0.092	0.095	2.16	2.34	2.41
I	0.176	0.180	0.184	4.47	4.57	4.67
J	0.018	0.020	0.023	0.46	0.51	0.58
K	0.038	0.040	0.044	0.97	1.01	1.12
L	0.018	0.020	0.023	0.46	0.52	0.58
P	0.042	0.047	0.052	1.06	1.20	1.32
Q	0.034	0.039	0.044	0.86	1.00	1.11
R	0.034	0.039	0.044	0.86	1.00	1.11
S	0.074	0.079	0.084	1.86	2.00	2.11

Dimensions – TO-252AA (D-Package) – D-PAK Surface Mount



Dimension	Inches			Millimeters		
	Min	Typ	Max	Min	Typ	Max
A	0.040	0.043	0.050	1.02	1.09	1.27
B	0.235	0.243	0.245	5.97	6.16	6.22
C	0.106	0.108	0.113	2.69	2.74	2.87
D	0.205	0.208	0.213	5.21	5.29	5.41
E	0.255	0.262	0.265	6.48	6.65	6.73
F	0.027	0.031	0.033	0.69	0.80	0.84
G	0.087	0.090	0.093	2.21	2.28	2.36
H	0.085	0.092	0.095	2.16	2.33	2.41
I	0.176	0.179	0.184	4.47	4.55	4.67
J	0.018	0.020	0.023	0.46	0.51	0.58
K	0.038	0.040	0.044	0.97	1.02	1.12
L	0.018	0.020	0.023	0.46	0.51	0.58
M	0.000	0.000	0.004	0.00	0.00	0.10
N	0.021	0.026	0.027	0.53	0.67	0.69
O	0°	0°	5°	0°	0°	5°
P	0.042	0.047	0.052	1.06	1.20	1.32
Q	0.034	0.039	0.044	0.86	1.00	1.11

Product Selector

Part Number	Voltage		Gate Sensitivity	Type	Package
	400V	600V			
SJxx12L	X	X	20mA	Standard SCR	TO-220L
SJxx12R	X	X	20mA	Standard SCR	TO-220R
SJxx12N	X	X	20mA	Standard SCR	TO-263
SJxx12V	X	X	20mA	Standard SCR	TO-251
SJxx12D	X	X	20mA	Standard SCR	TO-252
SJxx12L1	X	X	6mA	Standard SCR	TO-220L
SJxx12R1	X	X	6mA	Standard SCR	TO-220R
SJxx12N1	X	X	6mA	Standard SCR	TO-263
SJxx12V1	X	X	6mA	Standard SCR	TO-251
SJxx12D1	X	X	6mA	Standard SCR	TO-252
SJxx12L2	X	X	10mA	Standard SCR	TO-220L
SJxx12R2	X	X	10mA	Standard SCR	TO-220R
SJxx12N2	X	X	10mA	Standard SCR	TO-263

Note: xx = Voltage/10

Thyristors

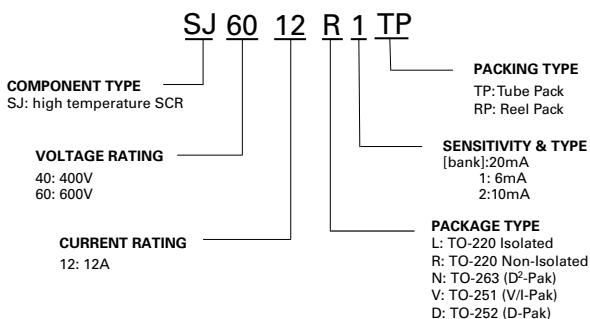
12 Amp High Junction Temperature SCRs

Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
SJxx12LxTP	SJxx12Ly	2.2g	Tube	1000 (50 per tube)
SJxx12RxTP	SJxx12Ry	2.2g	Tube	1000 (50 per tube)
SJxx12NxTP	SJxx12Ny	1.6g	Tube	1000 (50 per tube)
SJxx12NxRP	SJxx12Ny	1.6g	Embossed Carrier	500
SJxx12DxTP	SJxx12Dx	0.3 g	Tube	750 (75 per tube)
SJxx12DxRP	SJxx12Dx	0.3 g	Embossed Carrier	2500
SJxx12VxTP	SJxx12Vx	0.4 g	Tube	750 (75 per tube)

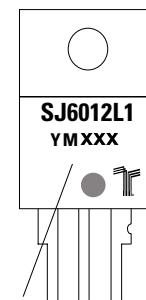
Note: xx=voltage/10, x=sensitivity

Part Numbering System



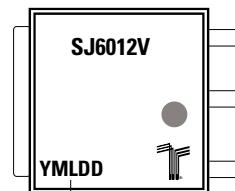
Part Marking System

TO-220 AB - (L and R Package)
TO-263 AB - (N Package)



Date Code Marking
Y:Year Code
M: Month Code
L: Location Code
DD: Calendar Code

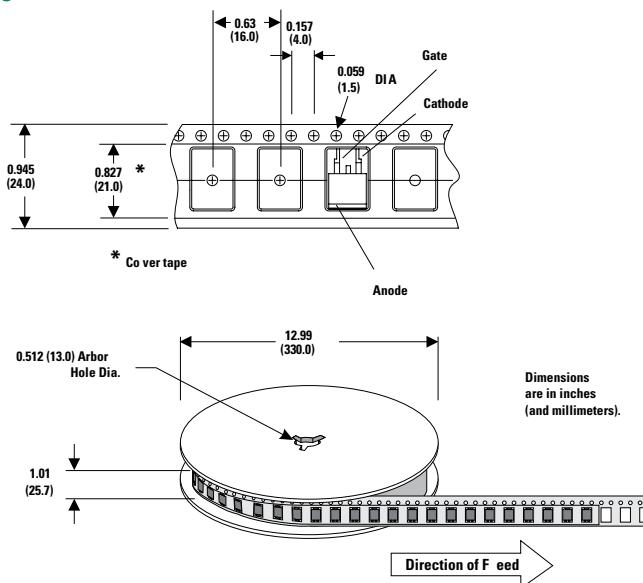
TO-251 (V/I-Pak)
TO-252 (D-Pak)



Date Code Marking
Y:Year Code
M: Month Code
L: Location Code
DD: Calendar Code

TO-263 Embossed Carrier Reel Pack (RP) Specifications

Meets all EIA-481-2 Standards



TO-252 Embossed Carrier Reel Pack (RP) Specifications

Meets all EIA-481-2 Standards

